



The products are 5-pin thyristor opto-couplers. The device combines an AlGaAs infrared emitting diode as the emitter which is optically coupled to a monolithic silicon zero-crossing photo triac in a plastic DIP5 package with different lead forming options. The products are widely used in solenoid/valve controls, lighting controls, motor controls, temperature controls, static AC power switches, solid state relays, interfacing microprocessors up to 265 V<sub>AC</sub> peripherals.

High isolation 5000 VRMS

DC input with zero-crossing photo triac output

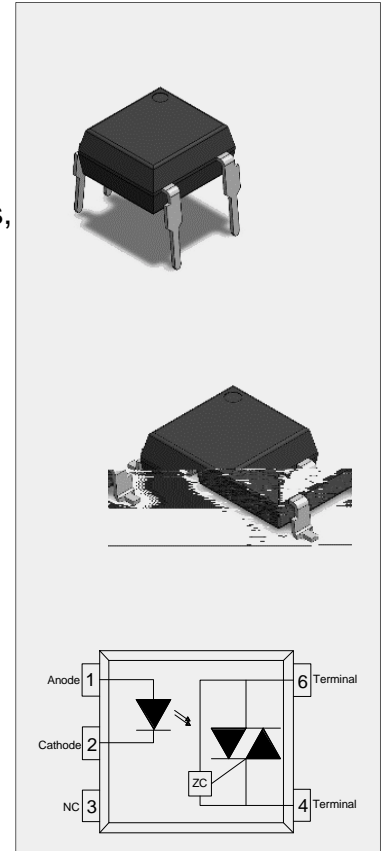
Operating temperature range -55

; ; CDM: C3

CQC approved

VDE approved

UL approved



(Temperature=25°C)

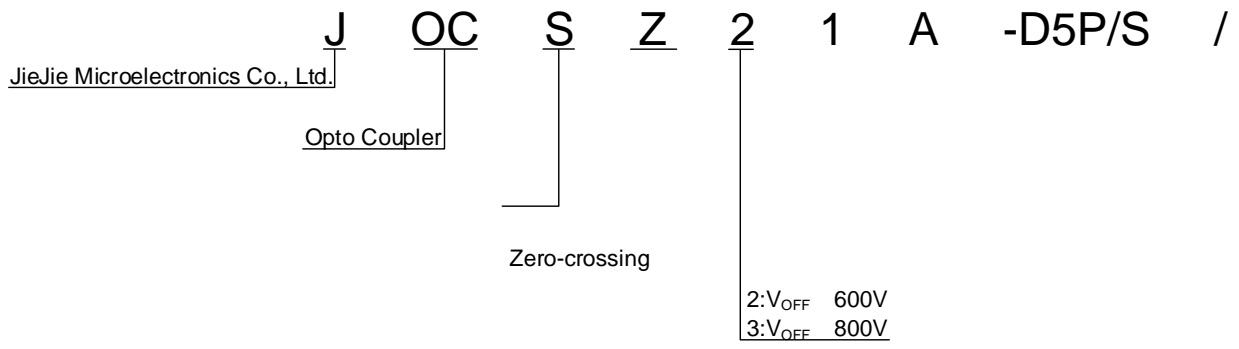
Parameter		Symbol	Value	Unit	
Input	Forward Current	I <sub>F</sub>	50	mA	
	Peak Forward Current	I <sub>FP</sub>	1	A	
	Reverse Voltage	V <sub>R</sub>	6	V	
	Power Dissipation	P <sub>D</sub>	75	mW	
Output	Off-state Output Terminal Voltage	V <sub>OFF</sub>	JOCSZ21X	600	V
			JOCSZ31X	800	
	Peak On-state Current (100μs pulse, 120 pps)	I <sub>TP</sub>	2	A	
	On-state RMS Current	I <sub>T(RMS)</sub>	100	mA	
	Peak Repetitive Surge Current (P <sub>w</sub> =10 ms)	I <sub>TSM</sub>	1.2	A	
Output Power Dissipation	P <sub>O</sub>	250	mW		
Total Power Dissipation		P <sub>tot</sub>	325	mW	
Isolation Voltage		V <sub>iso</sub>	5000	V <sub>rms</sub>	

Operating Temperature	$T_{opr}$	-55~110	
Junction Temperature	$T_j$	125	
Storage Temperature	$T_{stg}$	-55~125	
Soldering Temperature	$T_{sol}$	260	
Peak pulse voltage ( $T_j=25$ ; non-repetitive,off-state)	$V_{pp}$	1	kV

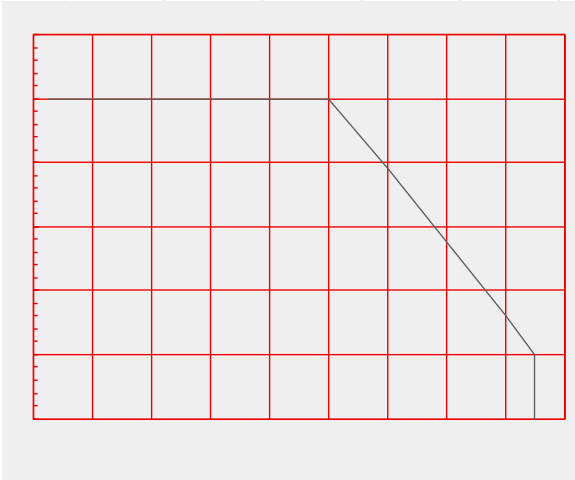
μ

(Temperature=25°C)

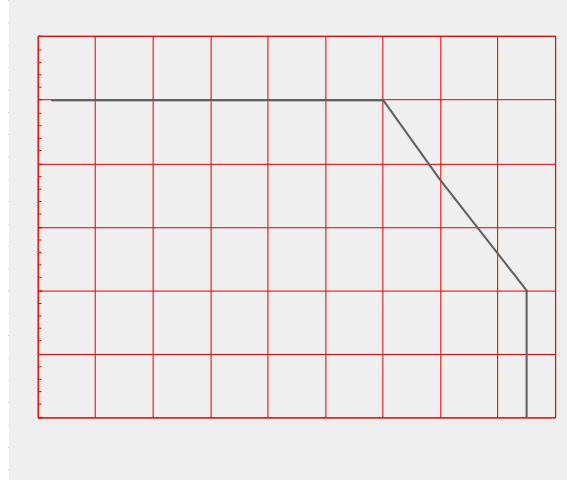
Parameter		Symbol	Condition	Min.	Typ.	Max.	Unit
Input	Forward Voltage	$V_F$	$I_F=10mA$	-	1.2	1.5	V
	Reverse Current	$I_R$	$V_R=6V$	-	-	1	μA
	Input Capacitance	$C_{in}$	$V=0, f=1kHz$	-	10	-	pF
Output	Peak Off-state Current, Either Direction	$I_{OFF}$	$V_{OFF}=Rated V_{OFF}$ $I_F=0$	-	-	100	nA
	Peak On-state Voltage, Either Direction	$V_{TM}$	$I_{TM}=100mA$	-	1.7	2.5	V
	Critical Rate of Rise of Off-state voltage	dV/dt	$V_{PEAK}= Rated V_{PEAK}$ $I_F=0$	2000	-	-	V/μs
Transfer Characteristics	LED Trigger Current	JOCSZ21A JOCSZ31A	Terminal Voltage=3V $I_{TM}=100mA$	-	-	10	mA
		JOCSZ21B JOCSZ31B		-	-	5	
		JOCSZ21C JOCSZ31C		-	-	3	
	Holding Current	$I_H$	$I_{TM}=2mA,$ $I_F=Rated I_{FT}$	-	500	-	μA
	Isolation Resistance	$R_{ISO}$	DC500V 40~60%R.H.	$10^{12}$	$10^{14}$	-	
	Floating Capacitance	$C_{IO}$	$V=0,$ $f=1MHz$	-	10	-	pF
	Response Time	$t_{on}$	$V_D=6V,$ $R_L=100$ , $I_F=20mA$	-	15	50	μs
Zero-crossing Characteristics	Inhibit Voltage	$V_{IH}$	$I_F=Rated I_{FT}$	-	-	20	V
	Leakage in Inhibited State	$I_{OFF2}$	$I_F=Rated I_{FT},$ $V_{OFF}=Rated V_{OFF}$	-	-	1.5	mA



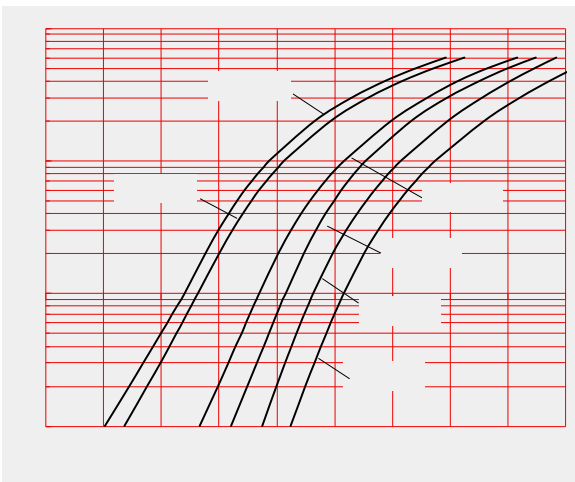
**FIG.1:** Max. Allowable LED Forward Current vs. Ambient Temperature



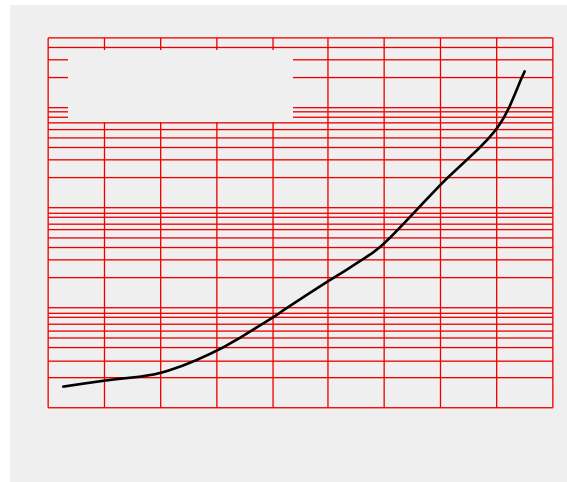
**FIG.2:** On-state Terminal Current vs. Ambient Temperature



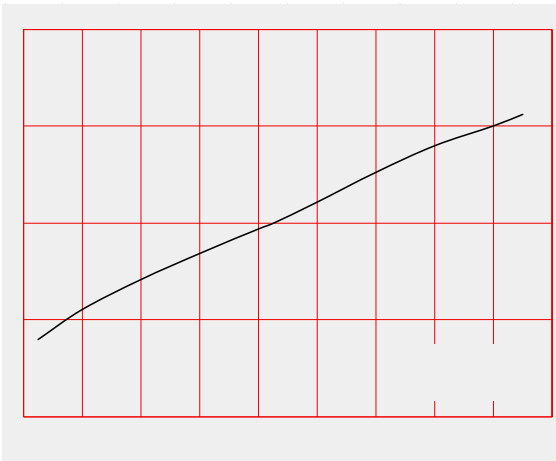
**FIG.3:** Forward Current vs. Forward Voltage



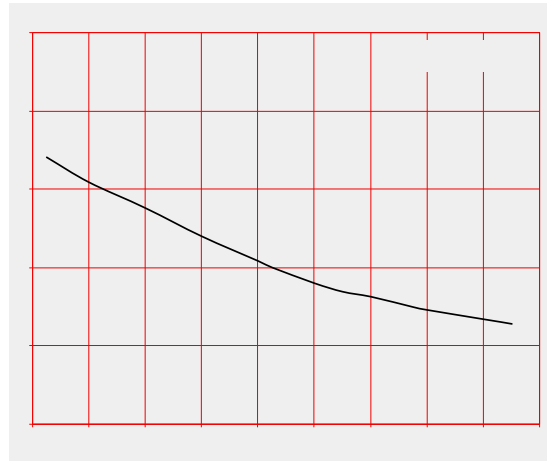
**FIG.4:** Normalized Off-state Terminal Current vs. Ambient Temperature



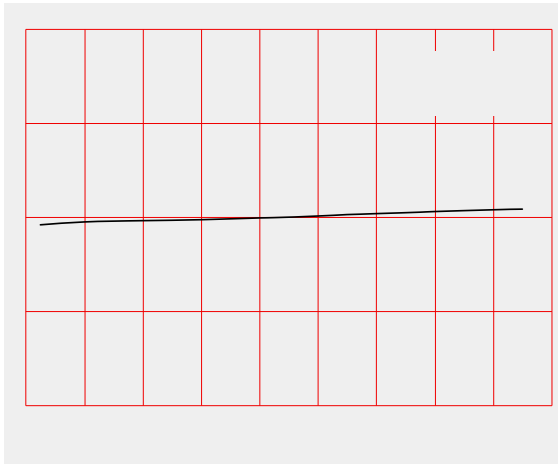
**FIG.5:** Normalized Off-state Terminal Voltage vs. Ambient Temperature



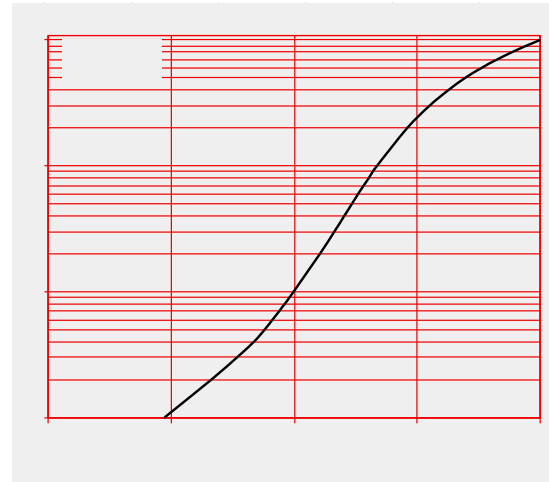
**FIG.6:** Normalized Trigger Current vs. Ambient Temperature



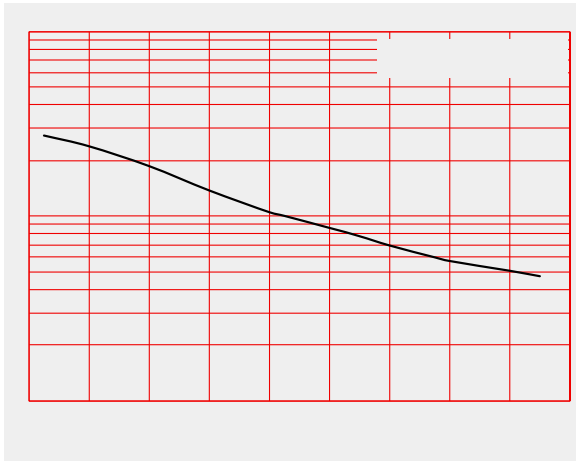
**FIG.7:** Normalized On-state Terminal Voltage vs. Ambient Temperature



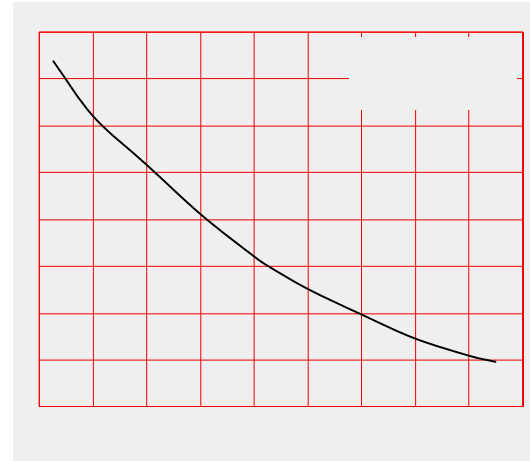
**FIG.8:** On-state Terminal Voltage vs. On-state Terminal Current



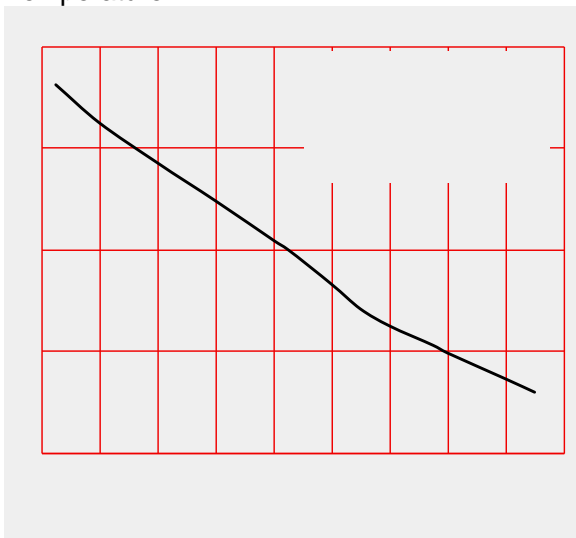
**FIG.9:** Normalized Holding Current vs. Ambient Temperature



**FIG.10:** Normalized Leakage in Inhibit State vs. Ambient Temperature

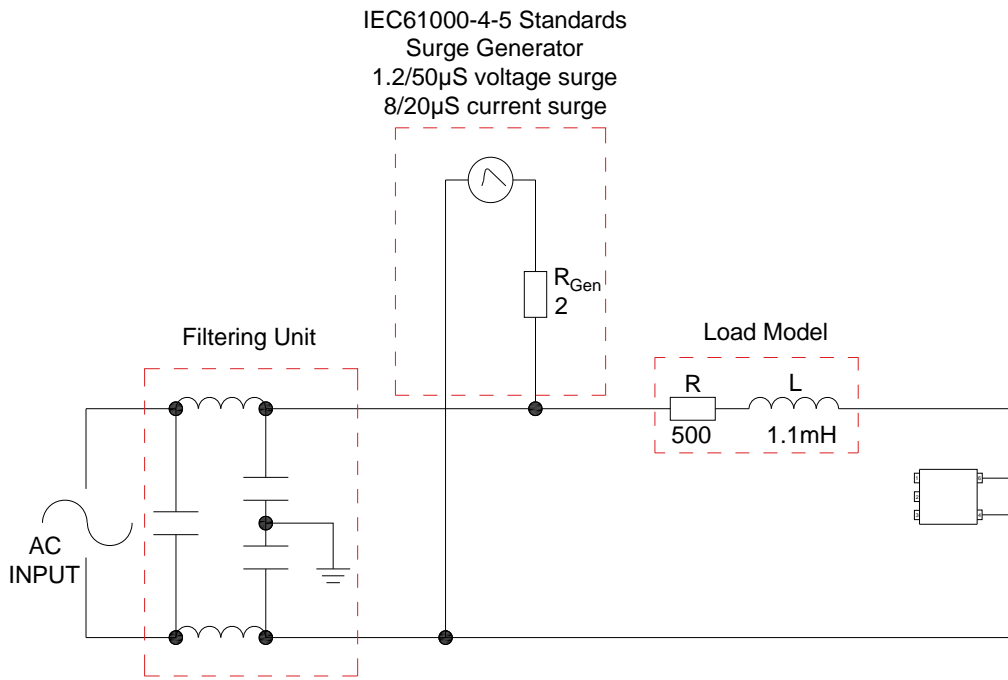


**FIG.11:** Normalized Inhibit Voltage vs. Ambient Temperature

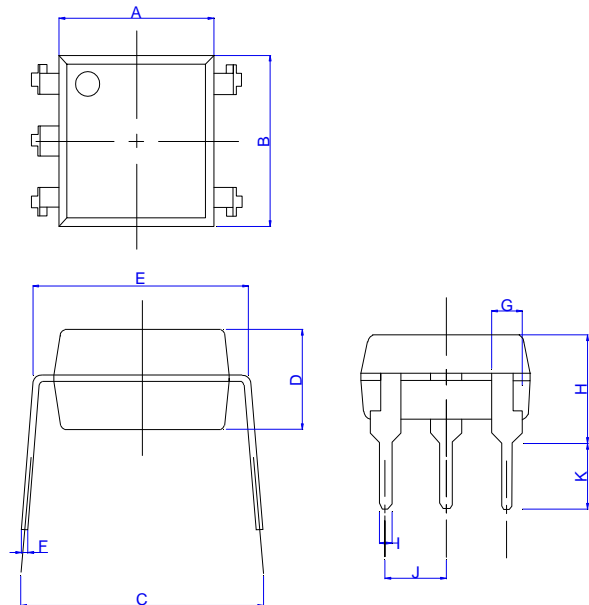


JOC SZ21X, JOC SZ31X

FIG.16: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



**Standard DIP Type:**

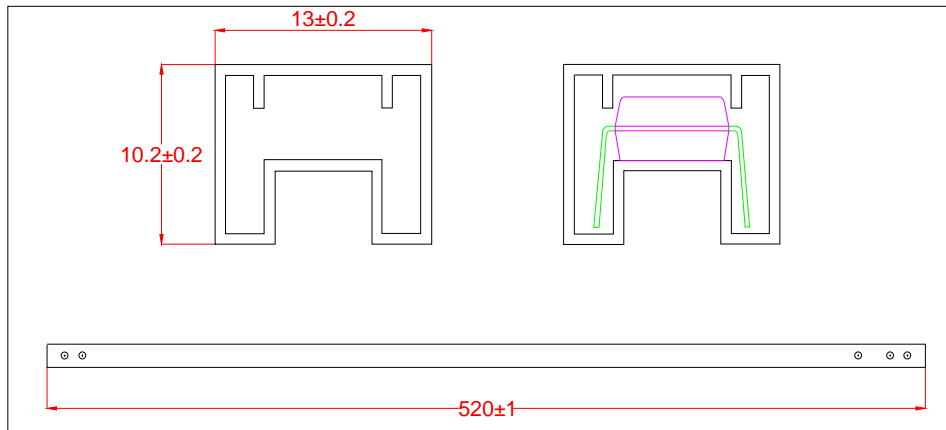


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	6.20		6.60	0.244		0.260
B	6.92		7.32	0.272		0.288
C	7.15		8.95	0.281		0.352
D	3.20		3.60	0.126		0.142
E	7.32		7.92	0.288		0.312
F	0.15		0.35	0.006		0.014
G	1.15		1.35	0.045		0.053
H	3.90		4.50	0.154		0.177
I	0.40		0.60	0.016		0.024
J	2.29		2.79	0.090		0.110
K	2.24		3.24	0.088		0.128

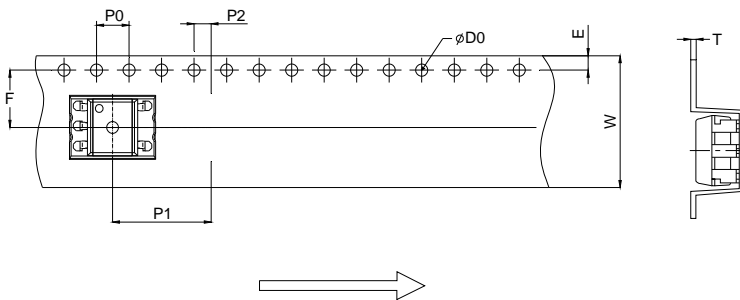
Option SMD Type:

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	6.20		6.60	0.244		0.260
B	6.92		7.32	0.272		0.288
C	9.50		10.50	0.375		0.413
D	3.20		3.60	0.126		0.142
E	7.32		7.92	0.288		0.312
F	0.05		0.35	0.002		0.014
G	0.16		0.36	0.006		0.014
H	0.60		1.40	0.024		0.055
I	0.90		1.50	0.035		0.059
J	3.30		3.90	0.130		0.154
K	2.29		2.79	0.090		0.110

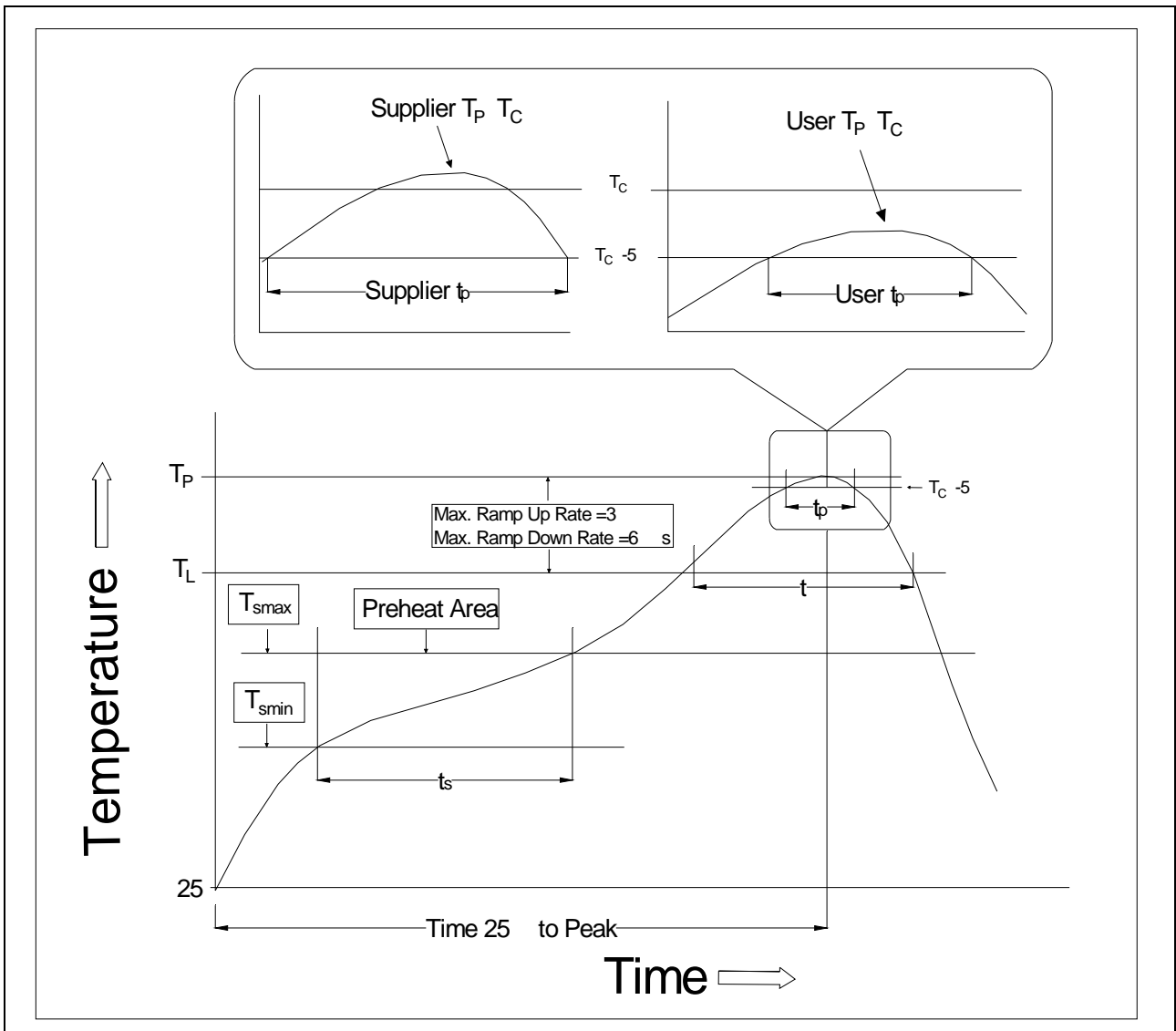
Standard DIP



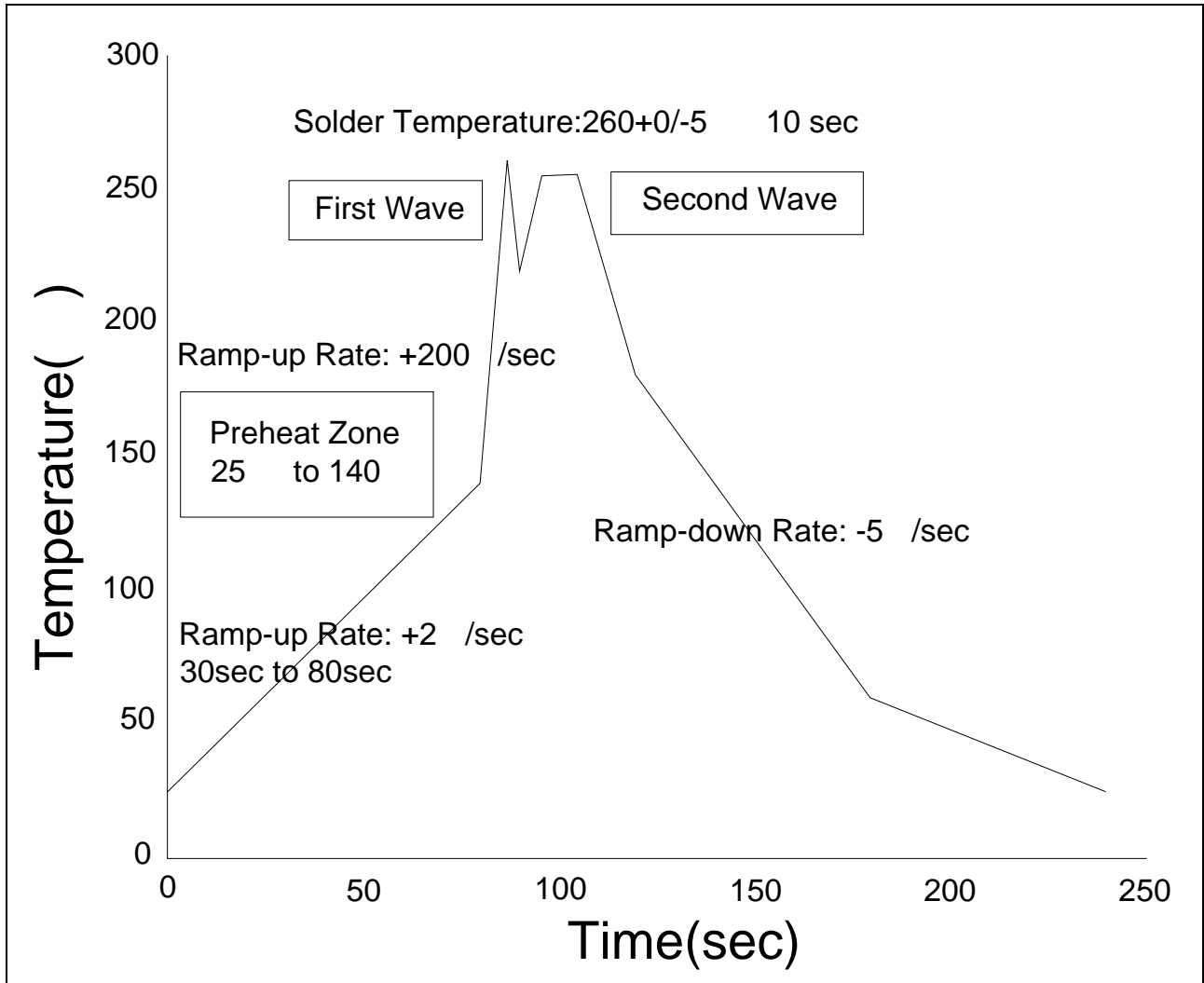
Option S/L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D0		1.50	1.60		0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	11.90	12.00	12.10	0.469	0.472	0.476
P2	1.90	2.00	2.10	0.075	0.079	0.083
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
T	0.35	0.40	0.45	0.014	0.016	0.018
W	15.70	16.00	16.30	0.618	0.630	0.642



Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. ( $T_{smin}$ )	100	150
Temperature Max. ( $T_{smax}$ )	150	200
Time ( $t_s$ ) from ( $T_{smin}$ to $T_{smax}$ )	60-120 seconds	60-120 seconds
Ramp-up Rate ( $t_L$ to $t_P$ )	3 $^\circ\text{C}/\text{second}$ max.	3 $^\circ\text{C}/\text{second}$ max.
Liquidus Temperature ( $T_L$ )	183	217
Time ( $t_L$ ) Maintained Above ( $T_L$ )	60-150 seconds	60-150 seconds
Peak Body Package Temperature	235 $+0$ $-5$	260 $+0$ $-5$
Time ( $t_P$ ) within 5 $^\circ\text{C}$ of 260	20 seconds	30 seconds
Ramp-down Rate ( $T_P$ to $T_L$ )	6 $^\circ\text{C}/\text{second}$ max.	6 $^\circ\text{C}/\text{second}$ max.
Time 25 $^\circ\text{C}$ to Peak Temperature	6 minutes max.	8 minutes max.




Soldering Temperature	360 ± 5
Soldering Time	3s max.

Note:

1. Reflow soldering is recommended at the temperatures and times shown, no more than three times.
2. Avoid direct contact between the epoxy body and any tools or surfaces exceeding its maximum storage temperature.
3. Application of pressure on the epoxy body is prohibited at elevated temperatures. In specific scenarios, any applied force must not exceed 2.5N.
4. Ensure the component has cooled to ambient temperature before proceeding with any subsequent manufacturing steps.
5. The component has a shelf life of one year when stored under standard conditions.
6. Recommend storage Temp.: 0~40°C;  
Recommend storage humidity: <60%;  
MSL level: MSL 1

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